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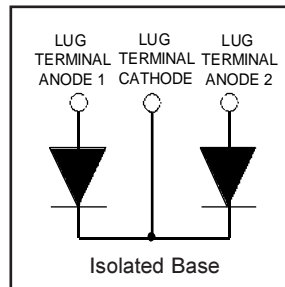
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HFA100MD60C

Ultrafast, Soft Recovery Diode

Features

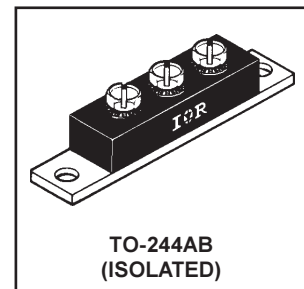
- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters



$V_R = 600V$
$V_F(\text{typ.})^{\textcircled{3}} = 1.1V$
$I_{F(AV)} = 100A$
$Q_{rr}(\text{typ.}) = 300nC$
$I_{RRM}(\text{typ.}) = 8A$
$t_{rr}(\text{typ.}) = 33ns$
$di_{(rec)M}/dt(\text{typ.})^{\textcircled{3}} = 240A/\mu s$

Description

HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



Absolute Maximum Ratings (per Leg)

	Parameter	Max.	Units
V_R	Cathode-to-Anode Voltage	600	V
$I_F @ T_C = 25^\circ C$	Continuous Forward Current	83	A
$I_F @ T_C = 100^\circ C$	Continuous Forward Current	40	
I_{FSM}	Single Pulse Forward Current ^①	400	
E_{AS}	Non-Repetitive Avalanche Energy ^②	220	μJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	180	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	71	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	C

Thermal - Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
R_{thJC}	Junction-to-Case, Single Leg Conducting	—	—	0.70	°C/W K/W
	Junction-to-Case, Both Legs Conducting	—	—	0.35	
R_{thCS}	Case-to-Sink, Flat , Greased Surface	—	0.10	—	
Wt	Weight	—	79 (2.8)	—	g (oz)
	Mounting Torque ^④	30 (3.4)	—	40 (4.6)	lbf•in
	Terminal Torque	30 (3.4)	—	40 (4.6)	(N•m)
	Vertical Pull	—	—	80	lbf•in
	2 inch Lever Pull	—	—	35	

Note: ^① Limited by junction temperature
^② L = 100μH, duty cycle limited by max T_J
^③ 125°C

^④ Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film of thermal grease to mounting surface. Gradually tighten each mounting bolt in 5-10 lbf•in steps until desired or maximum torque limits are reached. Module

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PD-2.442 rev. B 12/98

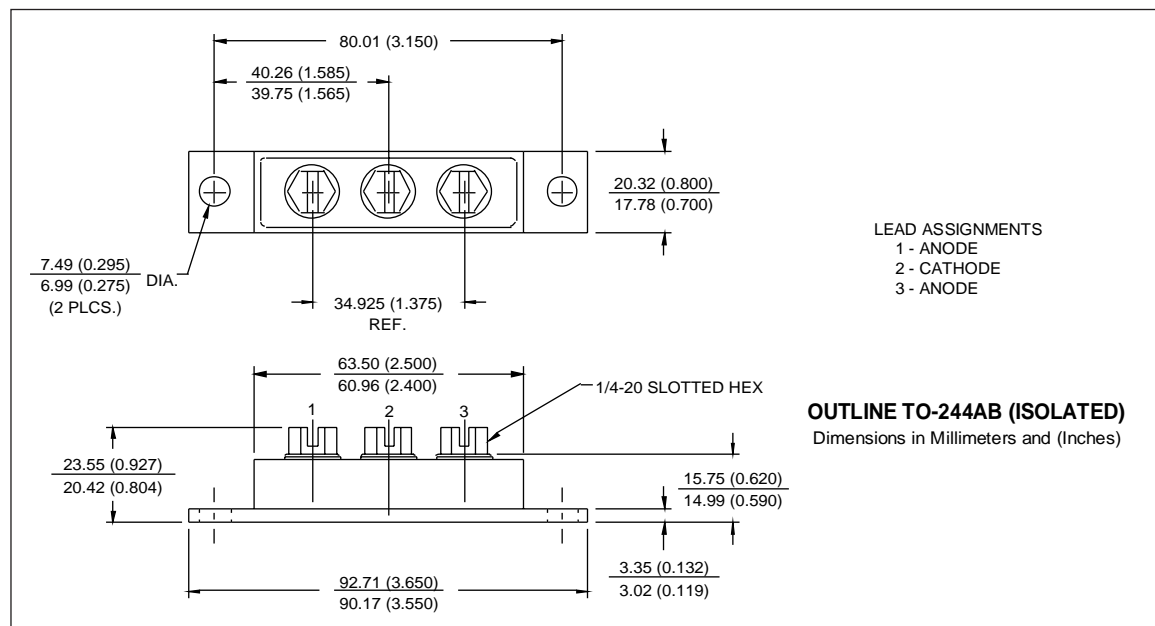
International
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Electrical Characteristics (per Leg) @ T_J = 25°C (unless otherwise specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
V _{BR} Cathode Anode Breakdown Voltage	600	—	—	V	I _R = 100μA
V _{FM} Max Forward Voltage	—	1.2	1.4	V	I _F = 50A
	—	1.4	1.6		I _F = 100A
	—	1.1	1.3		I _F = 50A, T _J = 125°C
I _{RM} Max Reverse Leakage Current	—	4.0	20	μA	V _R = V _R Rated
	—	1.0	4.0	mA	T _J = 125°C, V _R = 480V
C _T Junction Capacitance	—	140	250	pF	V _R = 200V
L _S Series Inductance	—	7.0	—	nH	From top of terminal hole to mounting plane

Dynamic Recovery Characteristics (per Leg) @ T_J = 25°C (unless otherwise specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
t _{rr} Reverse Recovery Time	—	33	—	ns	I _F = 1.0A, di _F /dt = 200A/μs, V _R = 30V
t _{rr1}	—	76	115		T _J = 25°C See Fig. 5
t _{rr2}	—	130	200		T _J = 125°C
I _R RM1 Peak Recovery Current	—	8.0	15	A	T _J = 25°C See Fig. 6
	—	12	22		T _J = 125°C
Q _{rr1} Reverse Recovery Charge	—	300	900	nC	T _J = 25°C See Fig. 7
	—	780	2200		T _J = 125°C
di _(rec) /dt1 Peak Rate of Fall of Recovery Current	—	340	—	A/μs	T _J = 25°C See Fig. 8
	di _(rec) /dt2 During t _b	—	240		—



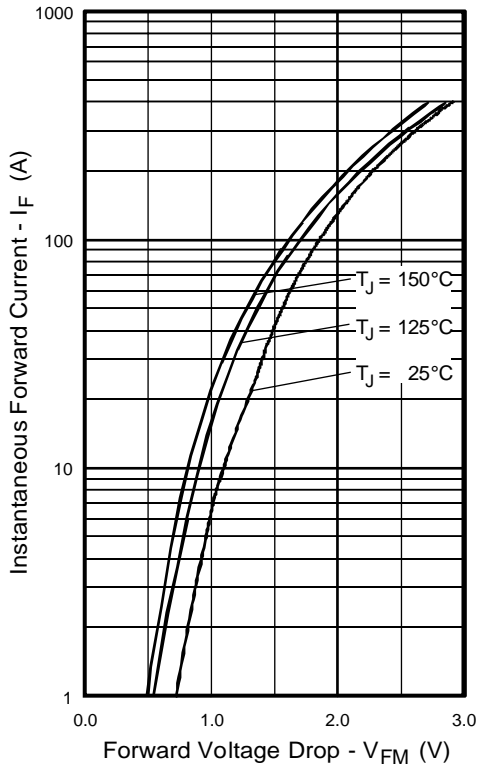


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current, (per Leg)

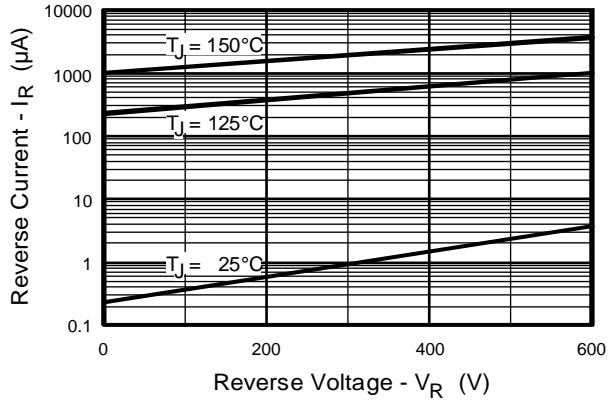


Fig. 2 - Typical Reverse Current vs. Reverse Voltage, (per Leg)

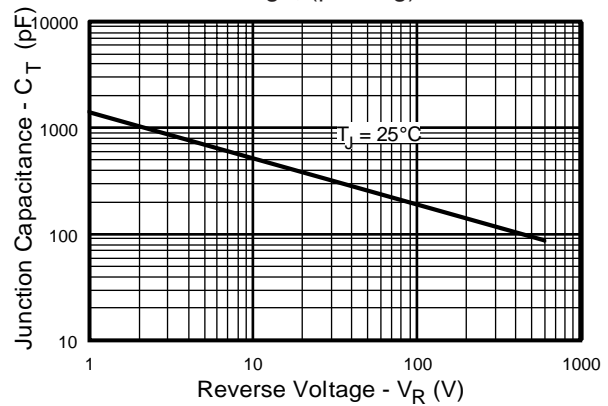


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, (per Leg)

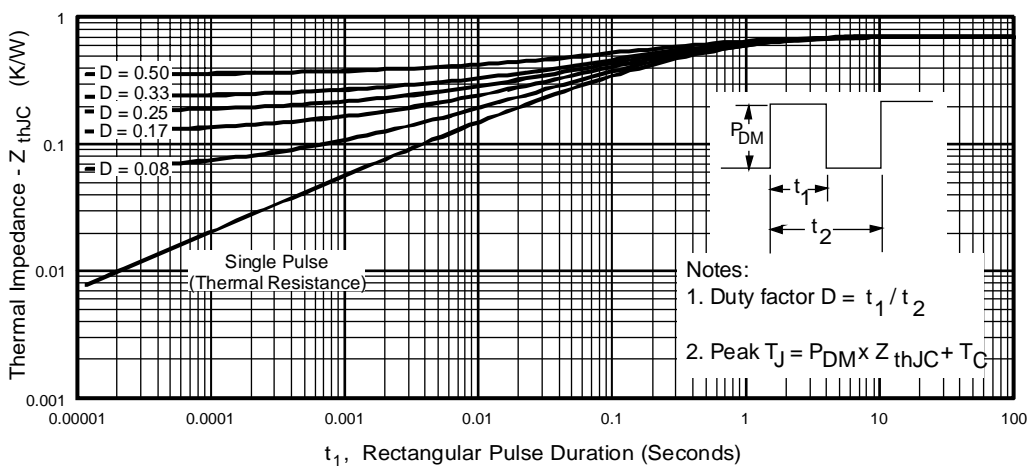


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics, (per Leg)

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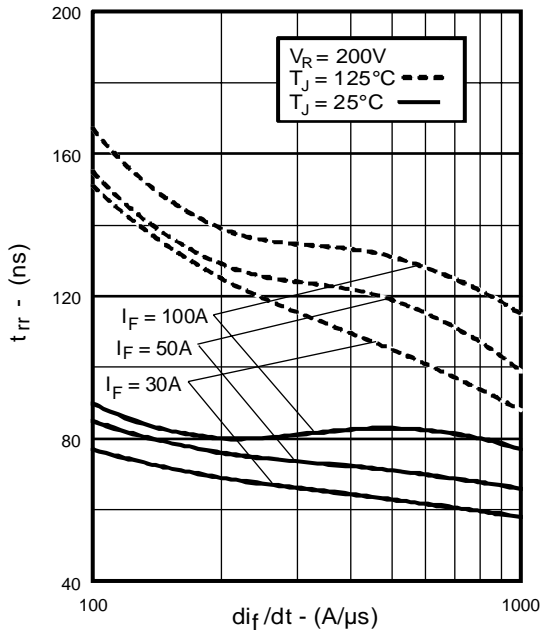


Fig. 5 - Typical Reverse Recovery vs. di_f/dt , (per Leg)

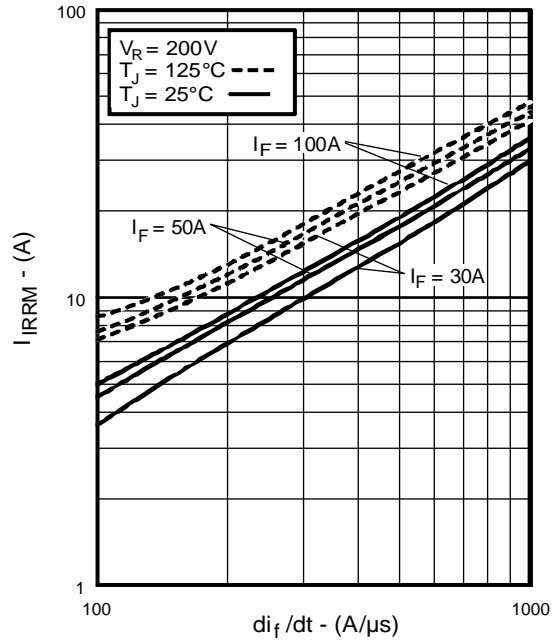


Fig. 6 - Typical Recovery Current vs. di_f/dt , (per Leg)

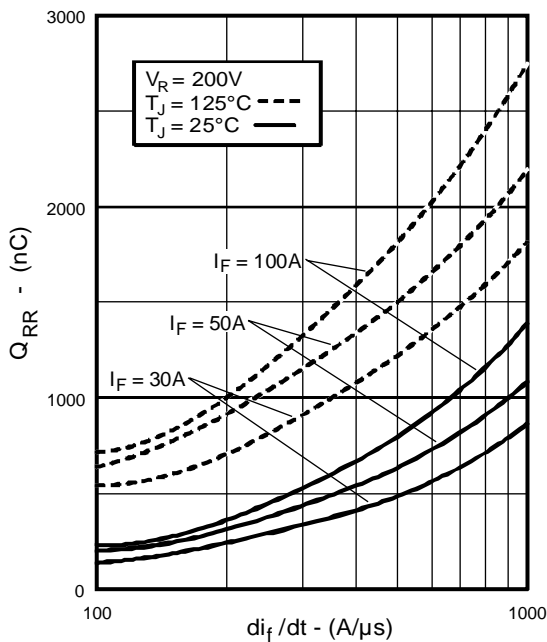


Fig. 7 - Typical Stored Charge vs. di_f/dt , (per Leg)

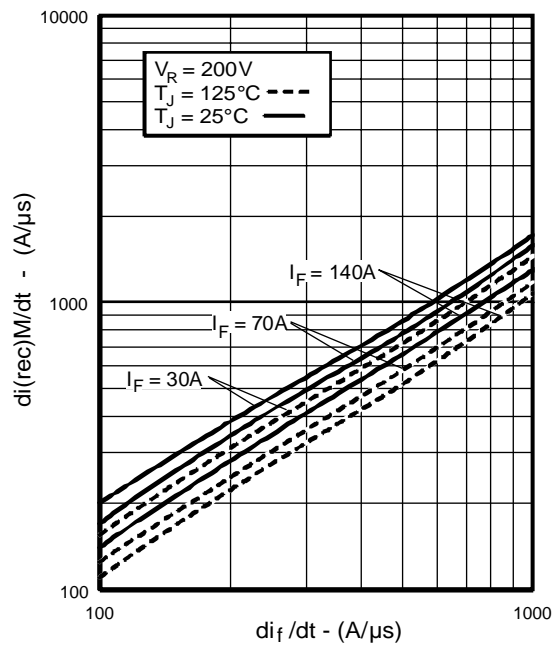


Fig. 8 - Typical $di_{(rec)}M/dt$ vs. di_f/dt , (per Leg)

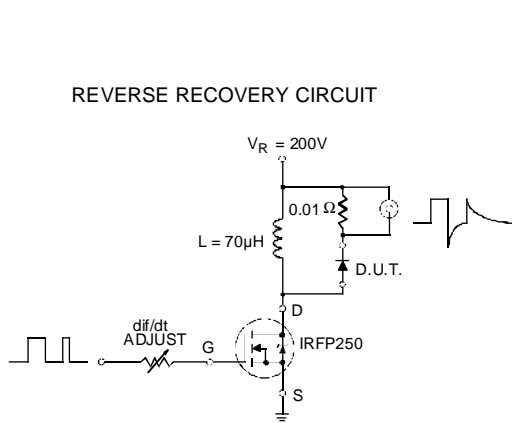


Fig. 9 - Reverse Recovery Parameter Test Circuit

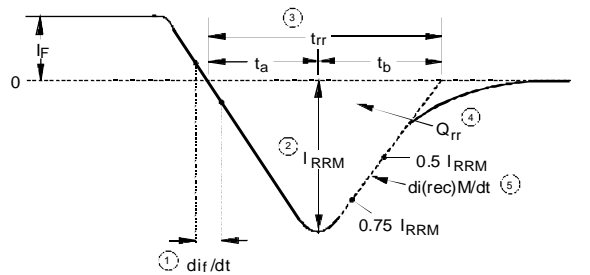


Fig. 10 - Reverse Recovery Waveform and Definitions

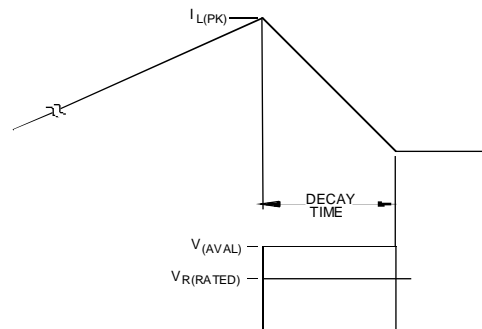
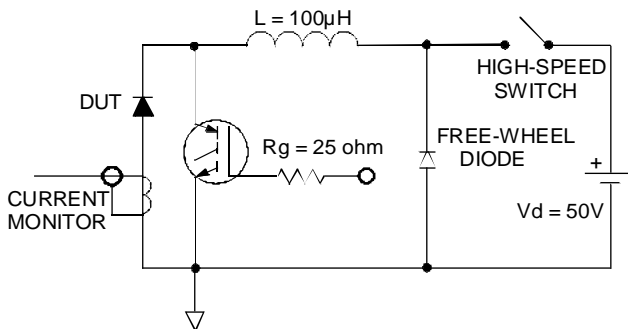


Fig. 11 - Avalanche Test Circuit and Waveforms